NXP USA Inc. - MKL13Z32VLK4 Datasheet

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	FlexIO, I²C, IrDA, SPI, UART/USART
Peripherals	DMA, PWM, WDT
Number of I/O	70
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 20x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-FQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl13z32vlk4

Table of Contents

1 Ratings

1.1 Thermal handling ratings

Table 1. Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.2 Moisture handling ratings

Table 2. Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.3 ESD handling ratings

Table 3. ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	–2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	–500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105 °C	–100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

Table 9. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_RUN}	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock disable 12 MHz core/6 MHz flash, V_{DD} = 3.0 V • at 25 °C • at 105 °C	 — —	 2.37 2.53	 2.56 2.73	mA	2
I_{DD_RUN}	Run mode current—48M HIRC mode, running CoreMark in Flash all peripheral clock enable 48 MHz core/24 MHz flash, V_{DD} = 3.0 V • at 25 °C • at 105 °C	 — —	 6.91 7.07	 7.19 7.35	mA	2
I_{DD_RUN}	Run mode current—48M HIRC mode, running While(1) loop in flash all peripheral clock disable, 48 MHz core/24 MHz flash, V_{DD} = 3.0 V • at 25 °C • at 105 °C	 — —	 4.14 4.3	 4.31 4.47	mA	
I_{DD_RUN}	Run mode current—48M HIRC mode, running While(1) loop in Flash all peripheral clock disable, 24 MHz core/12 MHz flash, V_{DD} = 3.0 V • at 25 °C • at 105 °C	 — —	 2.7 2.86	 2.92 3.09	mA	
I_{DD_RUN}	Run mode current—48M HIRC mode, Running While(1) loop in Flash all peripheral clock disable, 12 MHz core/6 MHz flash, V_{DD} = 3.0 V • at 25 °C • at 105 °C	 — —	 1.99 2.14	 2.15 2.31	mA	
I_{DD_RUN}	Run mode current—48M HIRC mode, Running While(1) loop in Flash all peripheral clock enable, 48 MHz core/24 MHz flash, V_{DD} = 3.0 V • at 25 °C • at 105 °C	 — —	 5.39 5.56	 5.61 5.78	mA	
I_{DD_VLPRCO}	Very Low Power Run Core Mark in Flash in Compute Operation mode: Core@4MHz, Flash @1MHz, V_{DD} = 3.0 V • at 25 °C	—	739	827.68	µA	
I_{DD_VLPRCO}	Very-low-power-run While(1) loop in SRAM in compute operation mode— 8 MHz LIRC mode, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	339	406.8	µA	
I_{DD_VLPRCO}	Very-low-power run While(1) loop in SRAM in compute operation mode:—2 MHz LIRC mode, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	152	197.6	µA	
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral					

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Table 9. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• at 50 °C • at 70 °C • at 85 °C • at 105 °C	— — — —	3.12 4.96 7.93 16.02	4.50 7.71 10.75 22.99		
I_{DD_LLS}	Low-leakage stop mode current with RTC current, at 1.8 V • at 25 °C and below • at 50 °C • at 70 °C • at 85 °C • at 105 °C	— — — — —	2.03 2.81 4.53 7.31 14.93	2.55 3.95 7.30 10.25 22.72	μA	3
I_{DD_VLLS3}	Very-low-leakage stop mode 3 current, all peripheral disable, at 3.0 V • at 25 °C and below • at 50 °C • at 70 °C • at 85 °C • at 105 °C	— — — — —	1.16 1.72 3.04 5.21 11.33	1.65 2.65 5.70 7.79 17.63	μA	
I_{DD_VLLS3}	Very-low-leakage stop mode 3 current with RTC current, at 3.0 V • at 25 °C and below • at 50 °C • at 70 °C • at 85 °C • at 105 °C	— — — — —	1.83 2.43 3.78 5.98 12.02	2.35 3.39 5.95 8.14 17.89	μA	3
I_{DD_VLLS3}	Very-low-leakage stop mode 3 current with RTC current, at 1.8 V • at 25 °C and below • at 50 °C • at 70 °C • at 85 °C • at 105 °C	— — — — —	1.58 2.13 3.37 5.4 10.99	1.98 3.17 5.80 7.83 16.86	μA	3
I_{DD_VLLS1}	Very-low-leakage stop mode 1 current all peripheral disabled at 3.0 V • at 25 °C and below • at 50°C • at 70°C	— — — —	0.62 0.99 1.88 3.41	1.06 1.43 2.65 4.53	μA	

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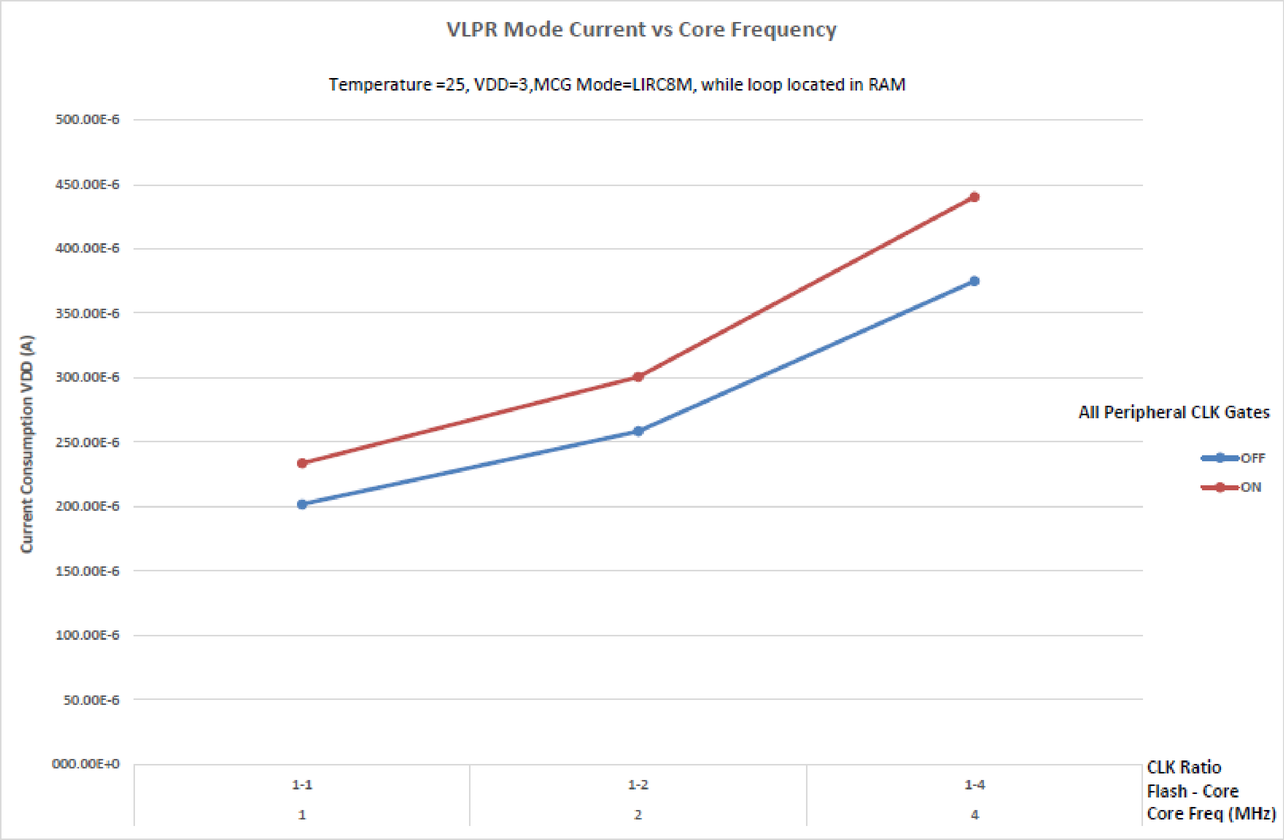

Figure 3. VLPR mode current vs. core frequency

2.2.6 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependent on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components, and MCU software operation play a significant role in the EMC performance. The system designer can consult the following Freescale applications notes, available on freescale.com for advice and guidance specifically targeted at optimizing EMC performance.

- AN2321: Designing for Board Level Electromagnetic Compatibility
- AN1050: Designing for Electromagnetic Compatibility (EMC) with HCMOS Microcontrollers
- AN1263: Designing for Electromagnetic Compatibility with Single-Chip Microcontrollers
- AN2764: Improving the Transient Immunity Performance of Microcontroller-Based Applications

2.3.2 General switching specifications

These general-purpose specifications apply to all signals configured for GPIO and UART signals.

Table 13. General switching specifications

Description	Min.	Max.	Unit	Notes
GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
External RESET and NMI pin interrupt pulse width — Asynchronous path	100	—	ns	2
GPIO pin interrupt pulse width — Asynchronous path	16	—	ns	2
Port rise and fall time	—	36	ns	3

1. The synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.
3. 75 pF load

2.4 Thermal specifications

2.4.1 Thermal operating requirements

Table 14. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_J	Die junction temperature	–40	125	°C	
T_A	Ambient temperature	–40	105	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + \theta_{JA} \times$ chip power dissipation.

2.4.2 Thermal attributes

NOTE

The 48 QFN, 32 QFN, and 64 MAPBGA packages for this product are not yet available. However, these packages are included in Package Your Way program for Kinetis MCUs. Visit freescale.com/KPYW for more details.

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG-Lite specifications

Table 17. IRC48M specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD48M}	Supply current	—	400	500	µA	
f_{irc48m}	Internal reference frequency	—	48	—	MHz	
$\Delta f_{irc48m\_ol\_lv}$	Open loop total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over temperature	—	± 0.5	± 1.5	$\%f_{irc48m}$	
$\Delta f_{irc48m\_ol\_hv}$	Open loop total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over temperature	—	± 0.5	± 1.0	$\%f_{irc48m}$	
J_{cyc_irc48m}	Period Jitter (RMS)	—	35	150	ps	
$t_{irc48mst}$	Startup time	—	2	3	µs	

Table 18. IRC8M/2M specification

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_2M}	Supply current in 2 MHz mode	—	14	17	µA	—
I_{DD_8M}	Supply current in 8 MHz mode	—	30	35	µA	—
f_{IRC_2M}	Output frequency	—	2	—	MHz	—
f_{IRC_8M}	Output frequency	—	8	—	MHz	—
$f_{IRC\_T\_2M}$	Output frequency range (trimmed)	—	—	±3	$\%f_{IRC}$	—
$f_{IRC\_T\_8M}$	Output frequency range (trimmed)	—	—	±3	$\%f_{IRC}$	—
T_{su_2M}	Startup time	—	—	12.5	µs	—
T_{su_8M}	Startup time	—	—	12.5	µs	—

3.3.2 Oscillator electrical specifications

Table 19. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x,C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.2.2 Oscillator frequency specifications

Table 20. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	1, 2
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Proper PC board layout procedures must be followed to achieve specifications.
2. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

3.4.1.3 Flash high voltage current behaviors

Table 23. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 24. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	—
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	—
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40\ °C \leq T_j \leq 125\ °C$.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

Using differential inputs can achieve better system accuracy than using single-end inputs.

Table 26. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
		- <12-bit modes	—	±0.4	–0.7 to +0.5		
E_{FS}	Full-scale error	- 12-bit modes - <12-bit modes	— —	–4 –1.4	–5.4 –1.8	LSB[4]	$V_{ADIN} = V_{DDA}$[5]
E_Q	Quantization error	- 16-bit modes - ≤13-bit modes	— —	–1 to 0 —	— ±0.5	LSB[4]	
ENOB	Effective number of bits	16-bit differential mode - Avg = 32 - Avg = 4 16-bit single-ended mode - Avg = 32 - Avg = 4	12.8 11.9 12.2 11.4	14.5 13.8 13.9 13.1	— — — —	bits bits bits bits	6
SINAD	Signal-to-noise plus distortion	See ENOB	6.02 × ENOB + 1.76			dB	
THD	Total harmonic distortion	16-bit differential mode - Avg = 32 16-bit single-ended mode - Avg = 32	— —	–94 –85	— —	dB dB	7
SFDR	Spurious free dynamic range	16-bit differential mode - Avg = 32 16-bit single-ended mode - Avg = 32	82 78	95 90	— —	dB dB	7
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$

3.6.4.2 12-bit DAC operating behaviors

Table 33. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	250	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	900	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2$ V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4$ V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance (load = 3 kΩ)	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/μs	
	• High power (SP_{HP})	1.2	1.7	—		
	• Low power (SP_{LP})	0.05	0.12	—		
BW	3dB bandwidth				kHz	
	• High power (SP_{HP})	550	—	—		
	• Low power (SP_{LP})	40	—	—		

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with $V_{DDA} > 2.4$ V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

5.1 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

Table 34. SPI master mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	2 x t_{periph}	2048 x t_{periph}	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	18	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	15	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	t_{periph} - 25	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}). For SPI1 f_{periph} is the system clock (f_{SYS}).
2. $t_{periph} = 1/f_{periph}$

Table 35. SPI master mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	2 x t_{periph}	2048 x t_{periph}	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} - 30	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	96	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—

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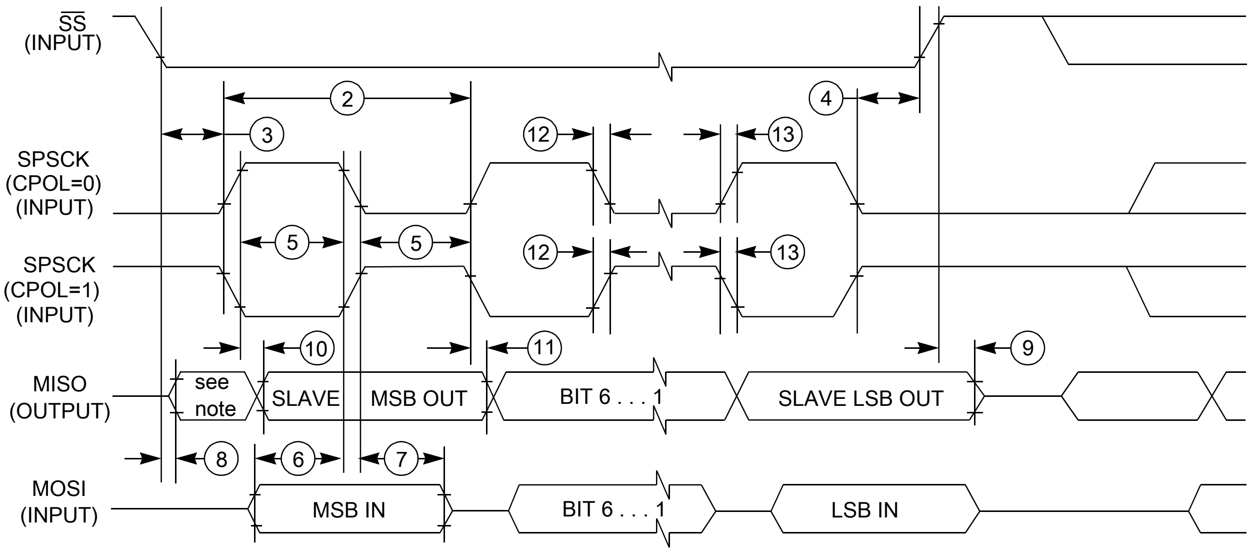

NOTE: Not defined

Figure 16. SPI slave mode timing (CPHA = 1)

5.2 I^{2}C

5.2.1 Inter-Integrated Circuit Interface (I2C) timing

Table 38. I2C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f_{SCL}	0	100	0	400[1]	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t_{HD}; STA	4	—	0.6	—	µs
LOW period of the SCL clock	t_{LOW}	4.7	—	1.25	—	µs
HIGH period of the SCL clock	t_{HIGH}	4	—	0.6	—	µs
Set-up time for a repeated START condition	t_{SU}; STA	4.7	—	0.6	—	µs
Data hold time for I^{2}C bus devices	t_{HD}; DAT	0[2]	3.45[3]	0[4]	0.9[2]	µs
Data set-up time	t_{SU}; DAT	250[5]	—	100[3], [6]	—	ns
Rise time of SDA and SCL signals	t_r	—	1000	20 +0.1C_b[7]	300	ns
Fall time of SDA and SCL signals	t_f	—	300	20 +0.1C_b[6]	300	ns
Set-up time for STOP condition	t_{SU}; STO	4	—	0.6	—	µs
Bus free time between STOP and START condition	t_{BUF}	4.7	—	1.3	—	µs
Pulse width of spikes that must be suppressed by the input filter	t_{SP}	N/A	N/A	0	50	ns

1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only be achieved when using the High drive pins across the full voltage range and when using the Normal drive pins and VDD ≥ 2.7 V.
2. The master mode I^2C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL lines.
3. The maximum tHD; DAT must be met only if the device does not stretch the LOW period (tLOW) of the SCL signal.
4. Input signal Slew = 10 ns and Output Load = 50 pF
5. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.
6. A Fast mode I^2C bus device can be used in a Standard mode I2C bus system, but the requirement $t_{SU;\ DAT} \geq 250$ ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line $t_{rmax} + t_{SU;\ DAT} = 1000 + 250 = 1250$ ns (according to the Standard mode I^2C bus specification) before the SCL line is released.
7. C_b = total capacitance of the one bus line in pF.

To achieve 1MHz I2C clock rates, consider the following recommendations:

- To counter the effects of clock stretching, the I2C baud Rate select bits can be configured for faster than desired baud rate.
- Use high drive pad and DSE bit should be set in PORTx_PCRn register.
- Minimize loading on the I2C SDA and SCL pins to ensure fastest rise times for the SCL line to avoid clock stretching.
- Use smaller pull up resistors on SDA and SCL to reduce the RC time constant.

Table 39. I^2C 1Mbit/s timing

Characteristic	Symbol	Minimum	Maximum	Unit
SCL Clock Frequency	f_{SCL}	0	1[1]	MHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t_{HD}; STA	0.26	—	µs
LOW period of the SCL clock	t_{LOW}	0.5	—	µs
HIGH period of the SCL clock	t_{HIGH}	0.26	—	µs
Set-up time for a repeated START condition	t_{SU}; STA	0.26	—	µs
Data hold time for I_2C bus devices	t_{HD}; DAT	0	—	µs
Data set-up time	t_{SU}; DAT	50	—	ns
Rise time of SDA and SCL signals	t_r	$20 + 0.1C_b$	120	ns
Fall time of SDA and SCL signals	t_f	$20 + 0.1C_b$[2]	120	ns
Set-up time for STOP condition	t_{SU}; STO	0.26	—	µs
Bus free time between STOP and START condition	t_{BUF}	0.5	—	µs
Pulse width of spikes that must be suppressed by the input filter	t_{SP}	0	50	ns

1. The maximum SCL Clock Frequency of 1Mbit/s can support maximum bus loading when using the High drive pins across the full voltage range.
2. C_b = total capacitance of the one bus line in pF.

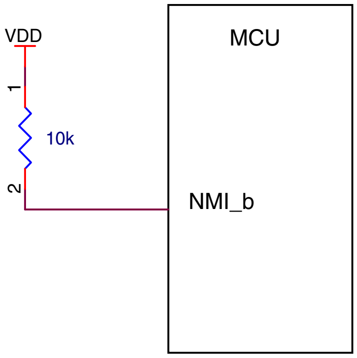

Figure 22. NMI pin biasing

- Debug interface

  This MCU uses the standard ARM SWD interface protocol as shown in the following figure. While pull-up or pull-down resistors are not required (SWD_DIO has an internal pull-up and SWD_CLK has an internal pull-down), external 10kΩ pull resistors are recommended for system robustness. Please note the RESET_b pin recommendations mentioned above.

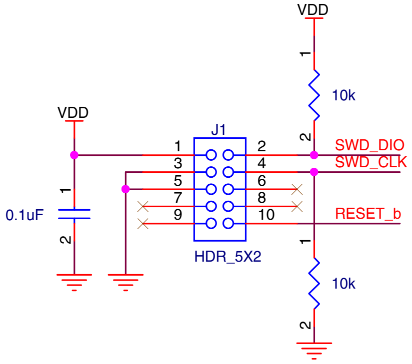

Figure 23. SWD debug interface

- Low leakage stop mode wakeup

  Select low leakage wakeup pins (LLWU_Px) to wake the MCU from one of the low leakage stop modes (LLS/VLLSx). Please refer to the signal multiplexing table for pin selection.

- Unused pin

  Unused GPIO pins should be left floating (no electrical connections) with the MUX field of the pin's PORTx_PCRn register equal to 0:0:0. This disables the digital input path to the MCU.

6.1.5 Crystal oscillator

When using an external crystal or ceramic resonator as the frequency reference for the MCU clock system, refer to the following table and diagrams.

The feedback resistor, RF, is incorporated internally with the low power oscillators. An external feedback is required when using high gain (HGO=1) mode.

The series resistor, RS, is required in high gain (HGO=1) mode when the crystal or resonator frequency is below 2MHz. Otherwise, the low power oscillator (HGO=0) must not have any series resistance; and the high frequency, high gain oscillator with a frequency above 2MHz does not require any series resistance.

Internal load capacitors (Cx, Cy) are provided in the low frequency (32.786kHz) mode. Use the SCxP bits in the OSC0_CR register to adjust the load capacitance for the crystal. Typically, values of 10pf to 16pF are sufficient for 32.768kHz crystals that have a 12.5pF CL specification. The internal load capacitor selection must not be used for high frequency crystals and resonators.

Table 40. External crystal/resonator connections

Oscillator mode	Oscillator mode
Low frequency (32.768kHz), low power	Diagram 1
Low frequency (32.768kHz), high gain	Diagram 2, Diagram 4
High frequency (1-32MHz), low power	Diagram 3
High frequency (1-32MHz), high gain	Diagram 4

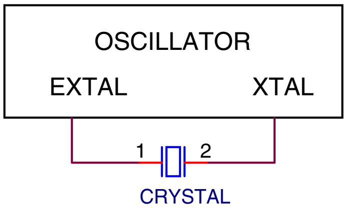

Figure 24. Crystal connection – Diagram 1

- Freescale Freedom Development Platform: http://www.freescale.com/freedom
- Tower System Development Platform: http://www.freescale.com/tower

IDEs for Kinetis MCUs

- Kinetis Design Studio IDE: http://www.freescale.com/kds
- Partner IDEs: http://www.freescale.com/kide

Development Tools

- PEG Graphics Software: http://www.freescale.com/peg
- Processor Expert Software and Embedded Components: http://www.freescale.com/processorexpert)

Run-time Software

- Kinetis SDK: http://www.freescale.com/ksdk
- Kinetis Bootloader: http://www.freescale.com/kboot
- ARM mbed Development Platform: http://www.freescale.com/mbed
- MQX RTOS: http://www.freescale.com/mqx

For all other partner-developed software and tools, visit http://www.freescale.com/partners.

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin QFN	98ASA00615D
48-pin QFN	98ASA00616D
64-pin LQFP	98ASS23234W
64-pin MAPBGA	98ASA00420D
80-pin LQFP	98ASS23174W

8 Pinouts and Packaging

8.1 KL13 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

NOTE

The 32 QFN, 48 QFN, and 64 MAPBGA packages for this product are not yet available. However, these packages are included in Package Your Way program for Kinetis MCUs. Visit freescale.com/KPYW for more details.

80 LQFP	64 LQFP	48 QFN	64 MAP BGA	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
—	—	—	C5	—	NC	NC	NC							
1	1	—	A1	1	PTE0	DISABLED		PTE0/ CLKOUT32K	SPI1_MISO	LPUART1_TX	RTC_CLKOUT	CMP0_OUT	I2C1_SDA	
2	2	—	B1	2	PTE1	DISABLED		PTE1	SPI1_MOSI	LPUART1_RX		SPI1_MISO	I2C1_SCL	
3	—	—	—	—	PTE2	DISABLED		PTE2	SPI1_SCK					
4	—	—	—	—	PTE3	DISABLED		PTE3	SPI1_MISO			SPI1_MOSI		
5	—	—	—	—	PTE4	DISABLED		PTE4	SPI1_PCS0					
6	—	—	—	—	PTE5	DISABLED		PTE5						
7	3	1	—	—	VDD	VDD	VDD							
8	4	2	C4	—	VSS	VSS	VSS							
9	5	3	E1	3	PTE16	ADC0_DP1/ ADC0_SE1	ADC0_DP1/ ADC0_SE1	PTE16	SPI0_PCS0	UART2_TX	TPM_CLKIN0		FXIO0_D0	
10	6	4	D1	4	PTE17	ADC0_DM1/ ADC0_SE5a	ADC0_DM1/ ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	TPM_CLKIN1	LPTMR0_ALT3	FXIO0_D1	
11	7	5	E2	5	PTE18	ADC0_DP2/ ADC0_SE2	ADC0_DP2/ ADC0_SE2	PTE18	SPI0_MOSI		I2C0_SDA	SPI0_MISO	FXIO0_D2	
12	8	6	D2	6	PTE19	ADC0_DM2/ ADC0_SE6a	ADC0_DM2/ ADC0_SE6a	PTE19	SPI0_MISO		I2C0_SCL	SPI0_MOSI	FXIO0_D3	
13	9	7	G1	—	PTE20	ADC0_DP0/ ADC0_SE0	ADC0_DP0/ ADC0_SE0	PTE20		TPM1_CH0	LPUART0_TX		FXIO0_D4	

	1	2	3	4	5	6	7	8	
A	PTE0	PTD7	PTD4/ LLWU_P14	PTD1	PTC11	PTC8	PTC6/ LLWU_P10	PTC5/ LLWU_P9	A
B	PTE1	PTD6/ LLWU_P15	PTD3	PTC10	PTC9	PTC7	PTC2	PTC4/ LLWU_P8	B
C	PTD5	PTD2	PTD0	VSS	NC	PTC1/ LLWU_P6/ RTC_CLKIN	PTB19	PTC3/ LLWU_P7	C
D	PTE17	PTE19	PTA0	PTA1	PTA3	PTB18	PTB17	PTC0	D
E	PTE16	PTE18	VSS	VDD	PTA2	PTB16	PTB2	PTB3	E
F	PTE21	PTE23	VSSA	VDDA	PTA5	PTB1	PTB0/ LLWU_P5	PTA20	F
G	PTE20	PTE22	VREFL	VREFH/ VREFO	PTA4	PTA13	VDD	PTA19	G
H	PTE29	PTE30	PTE31	PTE24	PTE25	PTA12	VSS	PTA18	H
	1	2	3	4	5	6	7	8	

Figure 30. 64 MAPBGA Pinout diagram

Figure below shows the 48 QFN pinouts:

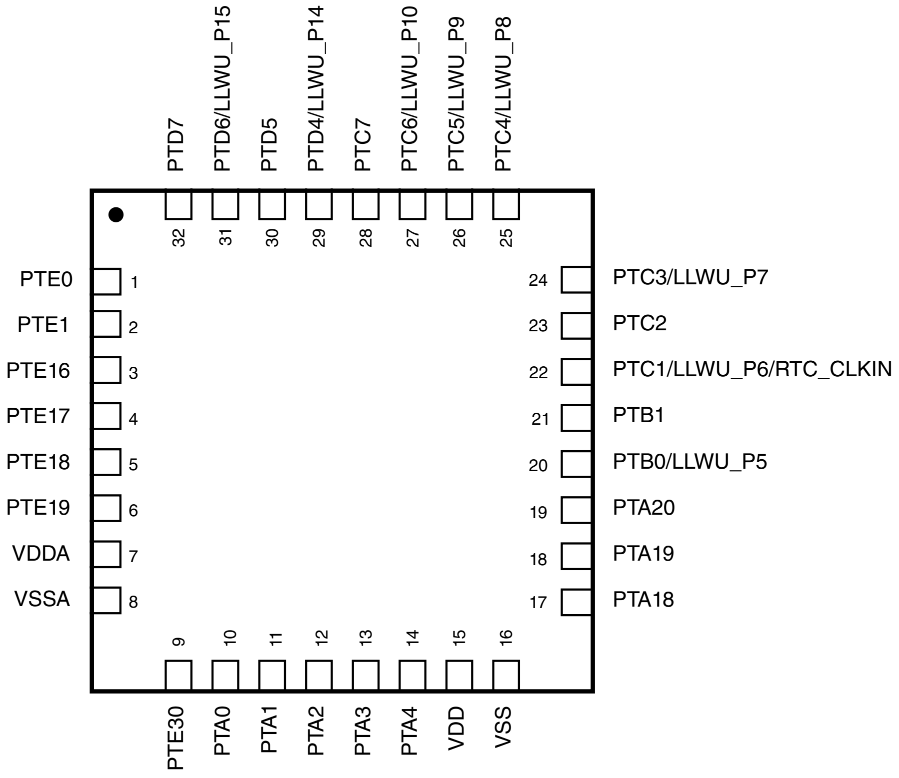

Figure 32. 32 QFN Pinout diagram

9 Ordering parts

9.1 Determining valid orderable parts

Valid orderable part numbers are provided on the Web. To determine the orderable part numbers for this device, go to freescale.com and perform a part number search for the following device numbers:

10 Part identification

10.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.